

**Legacy Device:** Motorola MC1490

The ML1490 is an integrated circuit featuring wide-range AGC for use in RF/IF amplifiers and audio amplifiers.

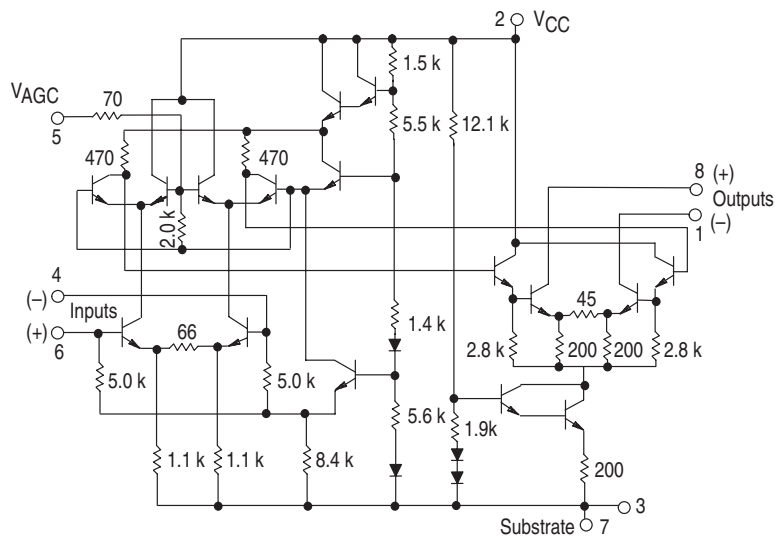
- High Power Gain:  
50 dB Typ at 10 MHz  
45 dB Typ at 60 MHz  
35 dB Typ at 100 MHz
- Wide Range AGC: 60 dB Min, DC to 60 MHz
- 6.0 V to 15 V Operation, Single Polarity Supply
- Operating Temperature Range  $T_A = -40^\circ$  to  $+85^\circ\text{C}$

Note: See Similar ML1350 For Possible Option

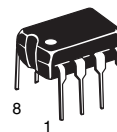
**MAXIMUM RATINGS** ( $T_A = +25^\circ\text{C}$ , unless otherwise noted.)

Rating	Symbol	Value	Unit
Power Supply Voltage	$V_{CC}$	+18	Vdc
AGC Supply	$V_{AGC}$	$V_{CC}$	Vdc
Input Differential Voltage	$V_{ID}$	5.0	Vdc
Operating Temperature Range	$T_A$	$-40$ to $+85$	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	$-65$ to $+150$	$^\circ\text{C}$
Junction Temperature	$T_J$	+150	$^\circ\text{C}$

**Representative Schematic Diagram**



Pins 3 and 7 should both be connected to circuit ground.



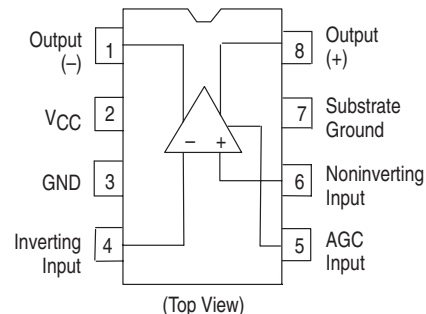
**P DIP 8 = PP**  
PLASTIC PACKAGE  
CASE 626

**CROSS REFERENCE/ORDERING INFORMATION**

PACKAGE	MOTOROLA	LANSDALE
P DIP 8	MC1490P	ML1490PP

**Note:** Lansdale lead free (**Pb**) product, as it becomes available, will be identified by a part number prefix change from **ML** to **MLE**.

**PIN CONNECTIONS**



**SCATTERING PARAMETERS**

( $V_{CC} = +12\text{ Vdc}$ ,  $T_A = +25^\circ\text{C}$ ,  $Z_0 = 50\ \Omega$ )

Parameter	Symbol	f = MHz Typ		Unit
		30	60	
Input Reflection Coefficient	$ S_{11} $ $\theta_{11}$	0.95 -7.3	0.93 -16	- deg
Output Reflection Coefficient	$ S_{22} $ $\theta_{22}$	0.99 -3.0	0.98 -5.5	- deg
Forward Transmission Coefficient	$ S_{21} $ $\theta_{21}$	16.8 128	14.7 64.3	- deg
Reverse Transmission Coefficient	$S_{12}$ $\theta_{12}$	0.00048 84.9	0.00092 79.2	- deg

ELECTRICAL CHARACTERISTICS (V<sub>CC</sub> = 12 Vdc, f = 60 MHz, BW = 1.0 MHz, T<sub>A</sub> = 25°C)

Characteristic	Figure	Symbol	Min	Typ	Max	Unit
Power Supply Current Drain	–	I <sub>CC</sub>	–	–	17	mA
AGC Range (AGC) 5.0 V Min to 7.0 V Max	19	M <sub>AGC</sub>	–60	–	–	dB
Output Stage Current (Sum of Pins 1 and 8)	–	I <sub>O</sub>	4.0	–	7.5	mA
Single-Ended Power Gain R <sub>S</sub> = R <sub>L</sub> = 50 Ω	19	G <sub>p</sub>	40	–	–	dB
Noise Figure R <sub>S</sub> = 50 Ohms	19	NF	–	6.0	–	dB
Power Dissipation	–	P <sub>D</sub>	–	168	204	mW

Figure 1. Unneutralized Power Gain versus Frequency (Tuned Amplifier, See Figure 19)

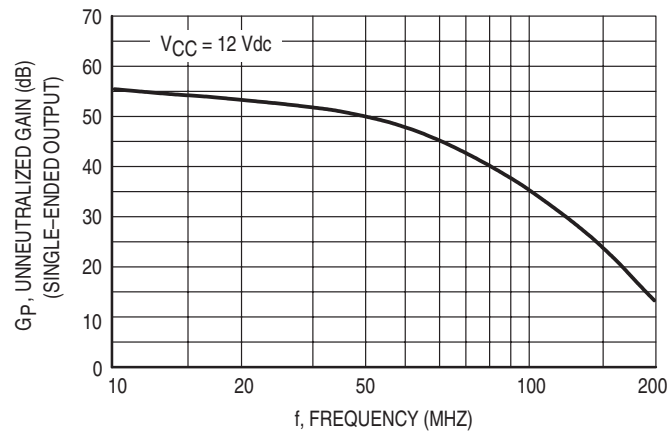


Figure 2. Voltage Gain versus Frequency (Video Amplifier, See Figure 20)

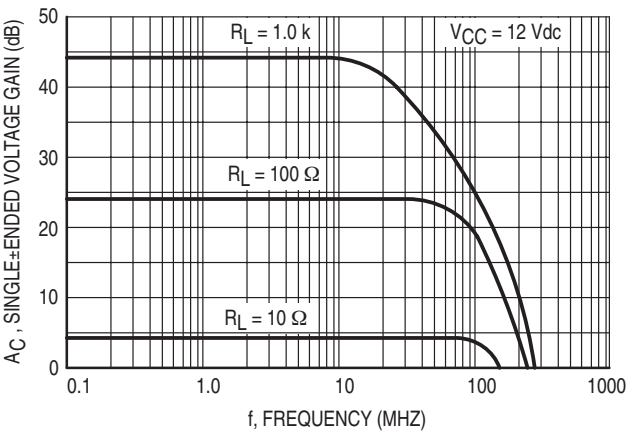


Figure 3. Dynamic Range: Output Voltage versus Input Voltage (Video Amplifier, See Figure 20)

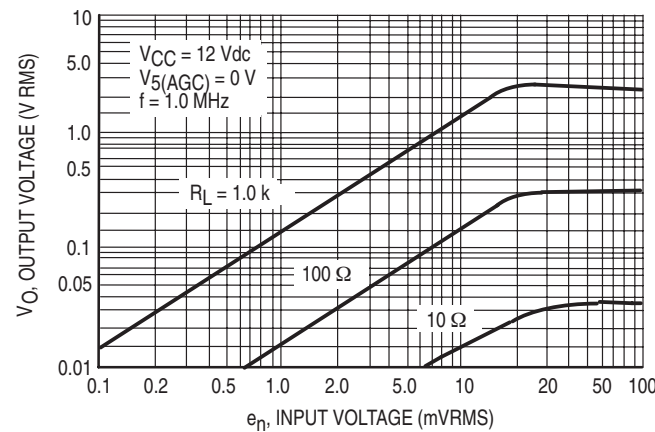
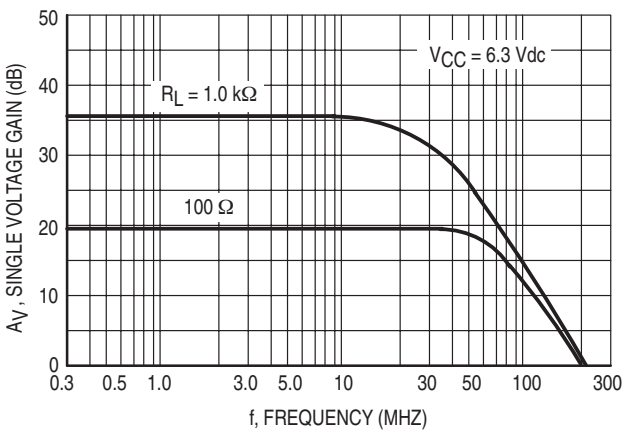
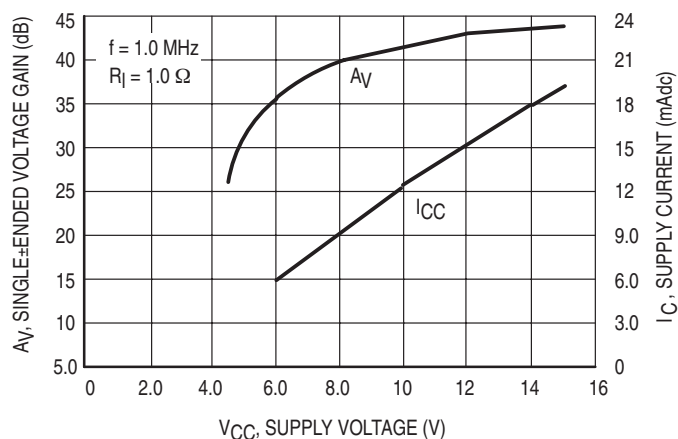
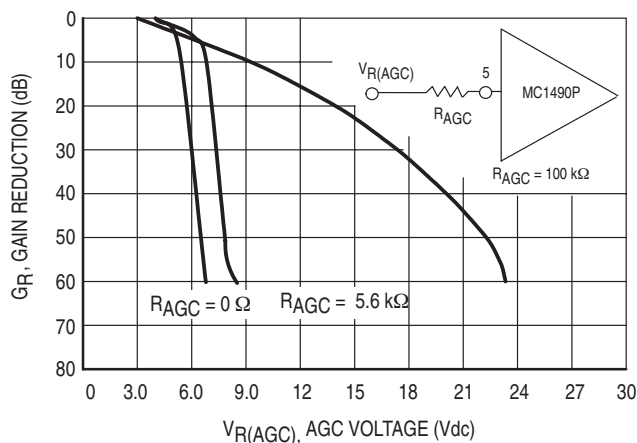
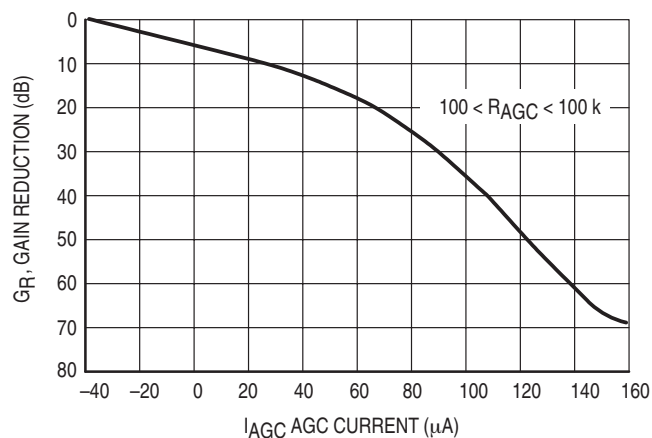
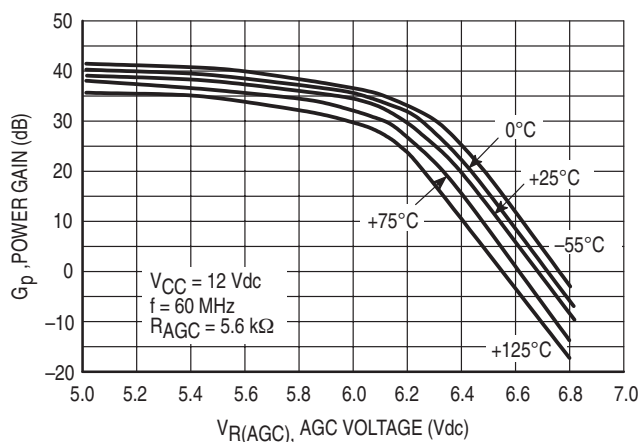
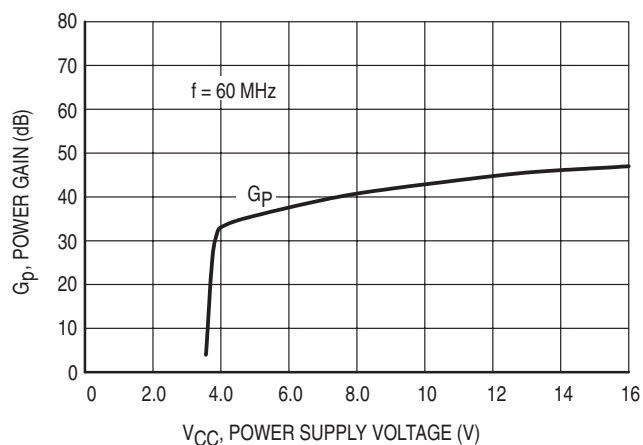
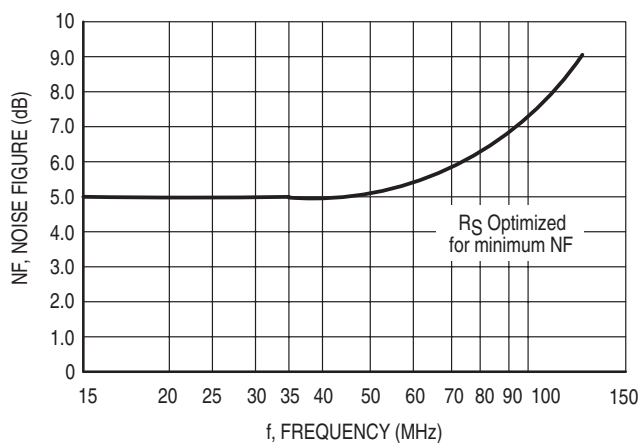


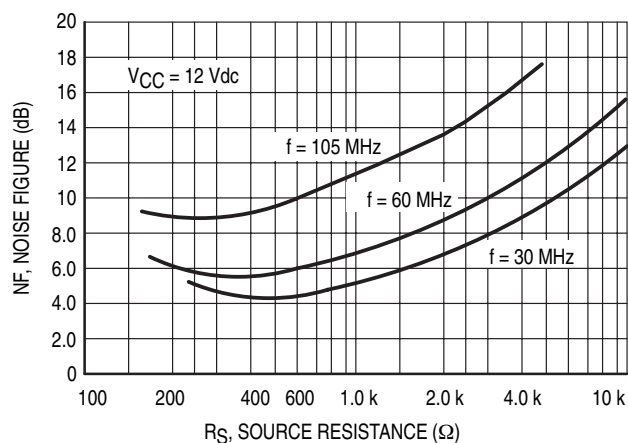
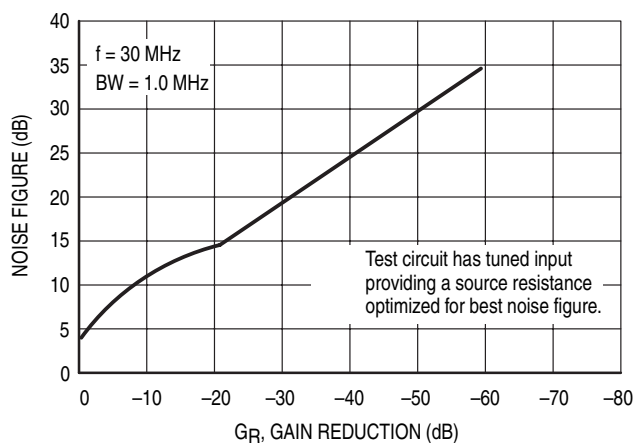
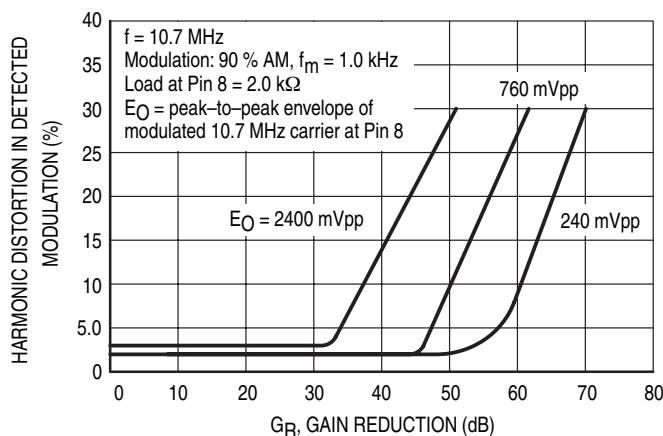
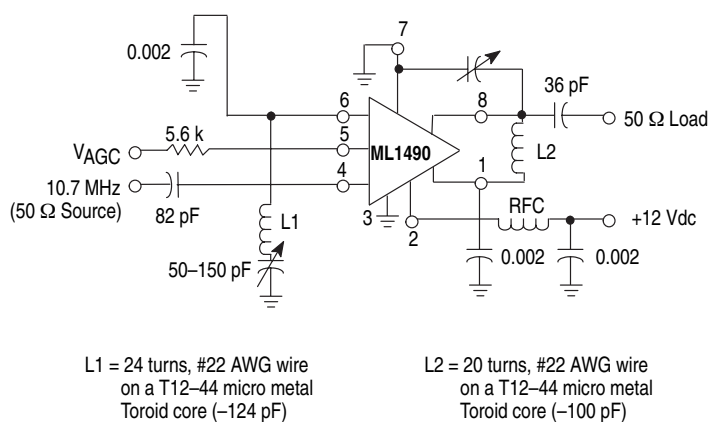
Figure 4. Voltage Gain versus Frequency (Video Amplifier, See Figure 20)



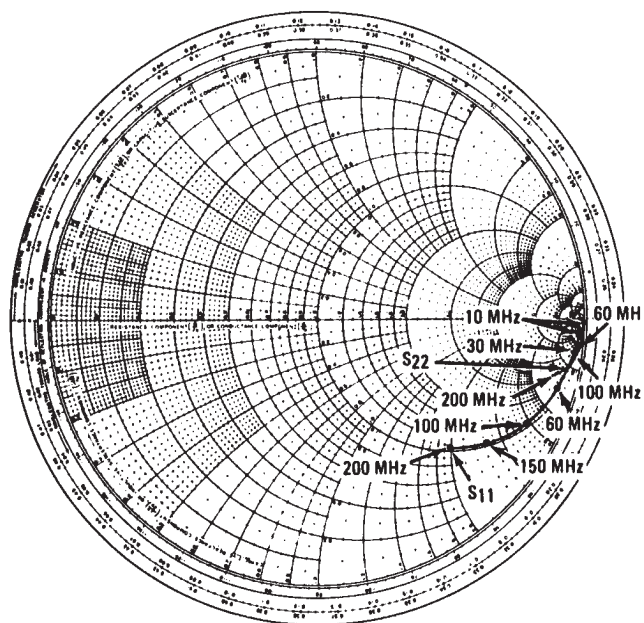
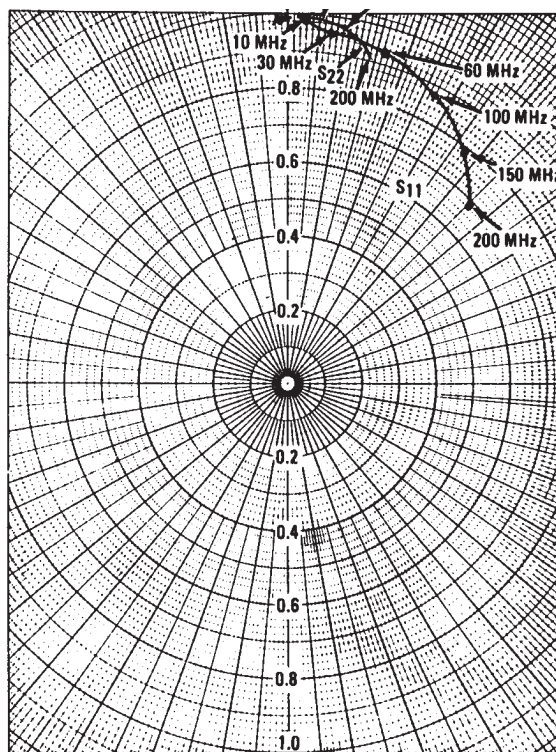
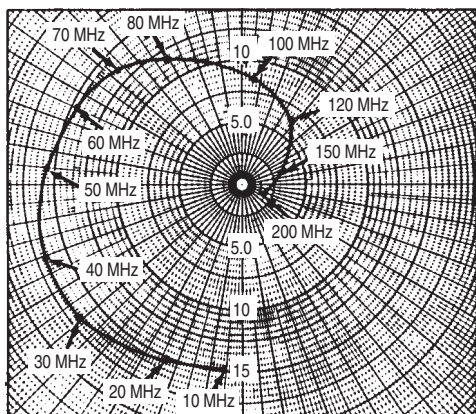
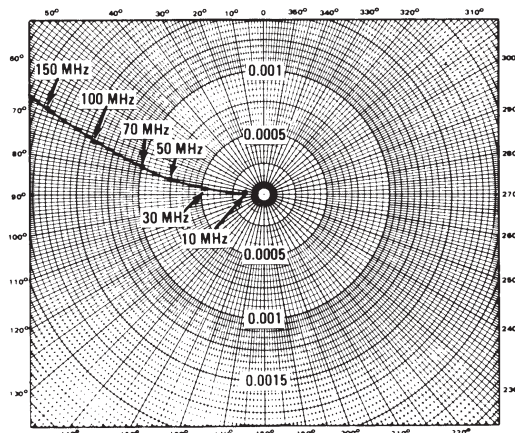
## Legacy Applications Information

**Figure 5. Voltage Gain and Supply Current versus Supply Voltage (Video Amplifier, See Figure 20)****Figure 6. Typical Gain Reduction versus AGC Voltage****Figure 7. Typical Gain Reduction versus AGC Current****Figure 8. Fixed Tuned Power Gain Reduction versus Temperature (See Test Circuit, Figure 19)****Figure 9. Power Gain versus Supply Voltage (See Test Circuit, Figure 19)****Figure 10. Noise Figure versus Frequency**

## Legacy Applications Information

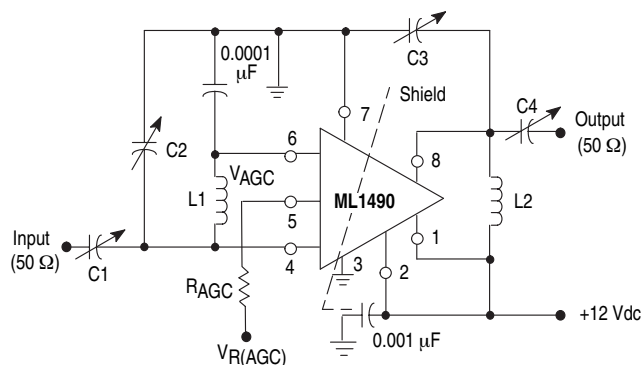
**Figure 11. Noise Figure versus Source Resistance****Figure 12. Noise Figure versus AGC Gain Reduction****Figure 13. Harmonic Distortion versus AGC Gain Reduction for AM Carrier (For Test Circuit, See Figure 14)****Figure 14. 10.7 MHz Amplifier Gain 55 dB, BW 100 kHz**

## Legacy Applications Information

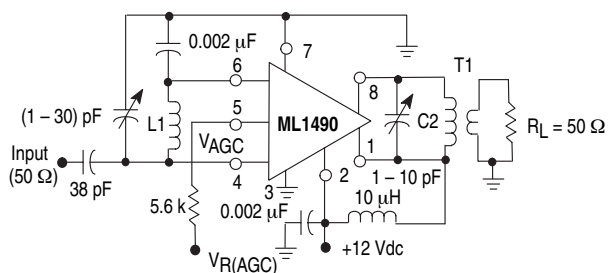
Figure 15.  $S_{11}$  and  $S_{22}$ , Input and Output Reflection CoefficientFigure 16.  $S_{11}$  and  $S_{22}$ , Input and Output Reflection CoefficientFigure 17.  $S_{21}$ , Forward Transmission Coefficient (Gain)Figure 18.  $S_{12}$ , Reverse Transmission Coefficient (Feedback)

## Legacy Applications Information

Figure 19. 60 MHz Power Gain Test Circuit



L1 = 7 turns, #20 AWG wire, 5/16" Dia., 5/8" long  
 L2 = 6 turns, #14 AWG wire, 9/16" Dia., 3/4" long  
 C1, C2, C3 = (1-30) pF  
 C4 = (1-10) pF

Figure 21. 30 MHz Amplifier  
(Power Gain = 50 dB, BW 1.0 MHz)

L1 = 12 turns, #22 AWG wire on a Toroid core,  
 (T37-6 micro metal or equiv).  
 T1: Primary = 17 turns, #20 AWG wire on a Toroid core, (T44-6).  
 Secondary = 2 turns, #20 AWG wire.

Figure 20. Video Amplifier

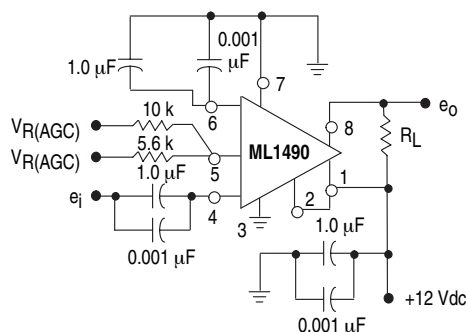
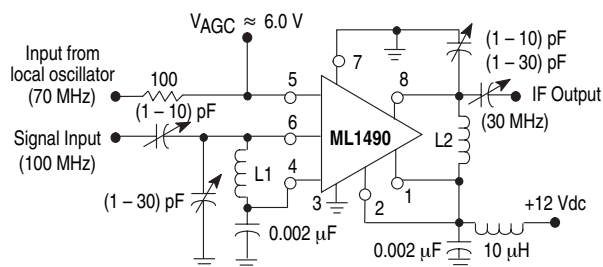
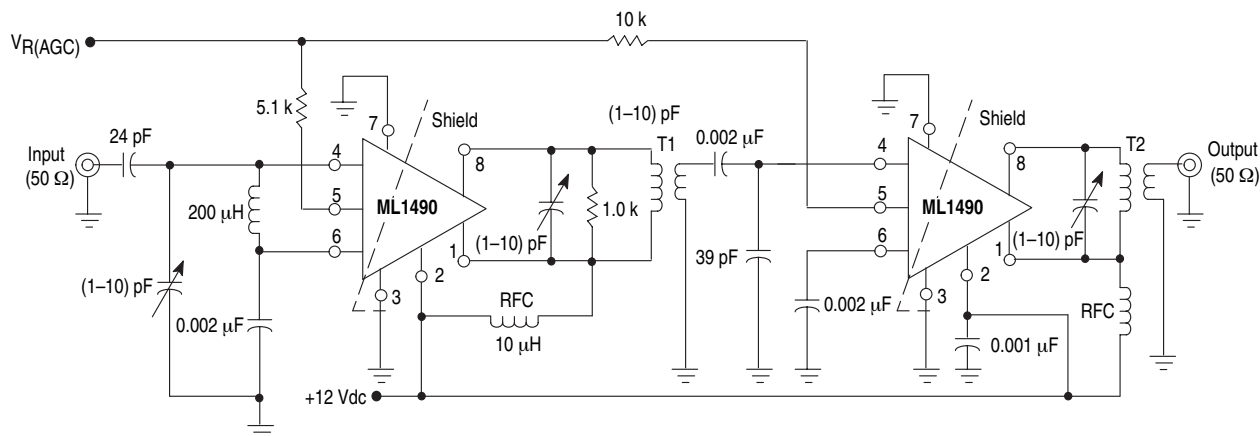


Figure 22. 100 MHz Mixer



L1 = 5 turns, #16 AWG wire, 1/4", ID Dia., 5/8" long  
 L2 = 16 turns, #20 AWG wire on a Toroid core, (T44-6).

Figure 23. Two-Stage 60 MHz IF Amplifier (Power Gain 80 dB, BW 1.5 MHz)



T1: Primary Winding = 15 turns, #22 AWG wire, 1/4" ID Air Core  
 Secondary Winding = 4 turns, #22 AWG wire,  
 Coefficient of Coupling  $\approx 1.0$

T2: Primary Winding = 10 turns, #22 AWG wire, 1/4" ID Air Core  
 Secondary Winding = 2 turns, #22 AWG wire,  
 Coefficient of Coupling  $\approx 1.0$

## DESCRIPTION OF SPEECH COMPRESSOR

The amplifier drives the base of a PNP transistor operating common-emitter with a voltage gain of approximately 20. The control R1 varies the quiescent Q point of this transistor so that varying amounts of signal exceed the level  $V_T$ . Diode D1 rectifies the positive peaks of Q1's output only when these peaks are greater than  $V_T \approx 7.0$  V. The resulting output is filtered by  $C_X$ ,  $R_X$ .

$R_X$  controls the charging time constant or attack time.  $C_X$  is involved in both charge and discharge.  $R_2$  (the 150 k $\Omega$  and input resistance of the emitter-follower Q2) controls the decay time. Making the decay long and attack short is accomplished by making  $R_X$  small and  $R_2$  large. (A Darlington emitter-follower may be needed if extremely slow decay times are required.)

The emitter-follower Q2 drives the AGC Pin 5 of the ML1490PP and reduces the gain. R3 controls the slope of signal compression.

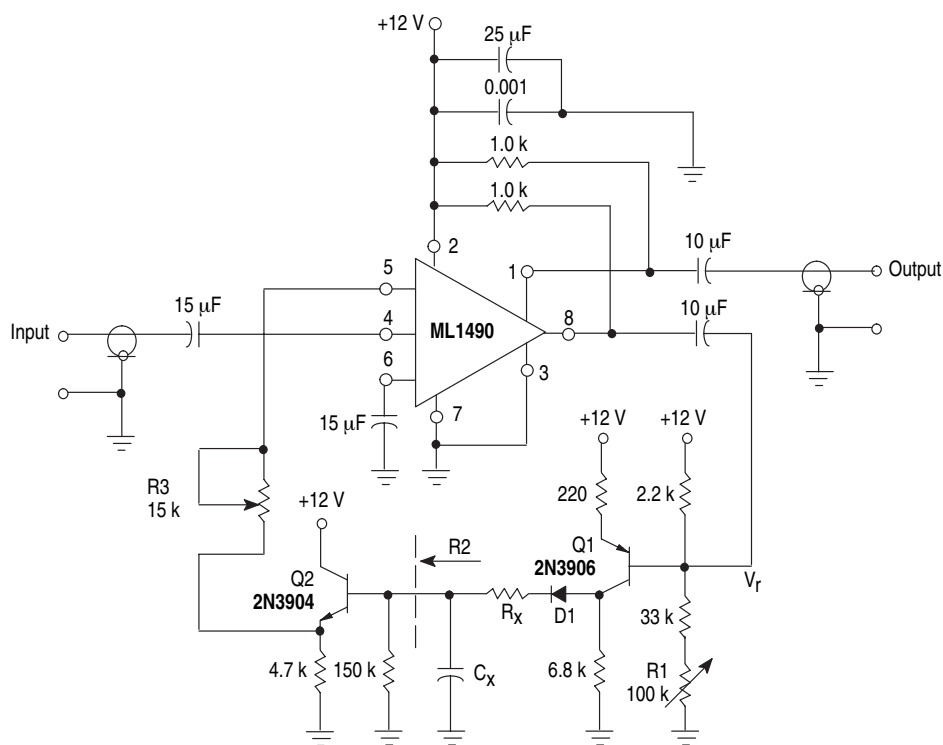
### Table 1. Distortion versus Frequency

Frequency	Distortion		Distortion	
	10 mV e <sub>i</sub>	100 mV e <sub>i</sub>	10 mV e <sub>i</sub>	100 mV e <sub>i</sub>
100 Hz	3.5%	12%	15%	27%
300 Hz	2%	10%	6%	20%
1.0 kHz	1.5%	8%	3%	9%
10 kHz	1.5%	8%	1%	3%
100 kHz	1.5%	8%	1%	3%
	Notes 1 and 2		Notes 3 and 4	

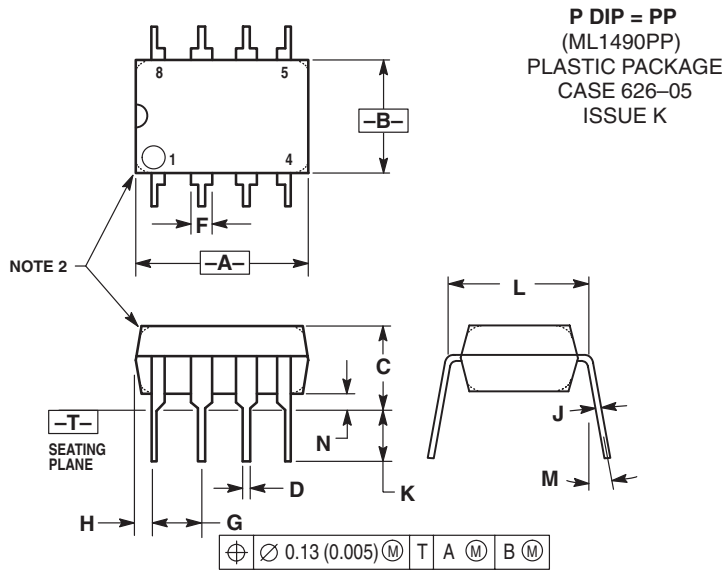
**Notes:**

(1) Decay = 300 ms Attack = 20 ms	(3) Decay = 20 ms Attack = 3.0 ms
(2) $C_X = 7.5 \mu F$ $R_X = 0$ (Short)	(4) $C_X = 0.68 \mu F$ $R_X = 1.5 k\Omega$

### Figure 24. Speech Compressor



OUTLINE DIMENSIONS



- NOTES:
- 1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
  - 2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
  - 3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.40	10.16	0.370	0.400
B	6.10	6.60	0.240	0.260
C	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
H	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300 BSC	
M	10°		10°	
N	0.76	1.01	0.030	0.040

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